

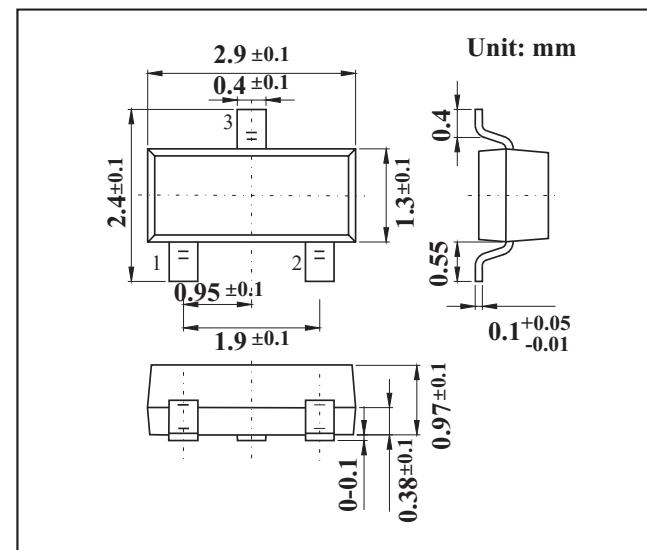
## SOT-23 Plastic-Encapsulate MOSFETS

### FEATURE

- TrenchFET Power MOSFET
- N-Channel 20-V(D-S) MOSFET

### MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



### MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	20	V
Gate-Source Voltage	V <sub>GS</sub>	±8	
Continuous Drain Current	I <sub>D</sub>	2.1	A
Continuous Source-Drain Current(Diode Conduction)	I <sub>S</sub>	0.6	
Power Dissipation	P <sub>D</sub>	0.4	W
Thermal Resistance from Junction to Ambient (t≤5s)	R <sub>θJA</sub>	312.5	°C/W
Operating Junction	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~+150	

## RATINGS AND CHARACTERISTIC CURVES

**MOSFET ELECTRICAL CHARACTERISTICS** Ta=25 °C unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Static</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10µA	20			V
Gate-threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 50µA	0.65	0.95	1.2	
Gate-body leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±8V			±100	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V			1	µA
Drain-source on-resistance <sup>a</sup>	R <sub>D(on)</sub>	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 3.6A		0.035	0.060	Ω
		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 3.1A		0.045	0.115	
Forward transconductance <sup>a</sup>	g <sub>f</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 3.6A		8		S
Diode forward voltage	V <sub>SD</sub>	I <sub>S</sub> = 0.94A, V <sub>GS</sub> = 0V		0.76	1.2	V
<b>Dynamic</b>						
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 3.6A		4.0	10	nC
Gate-source charge	Q <sub>gs</sub>			0.65		
Gate-drain charge	Q <sub>gd</sub>			1.5		
Input capacitance <sup>b</sup>	C <sub>iss</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1MHz		300		pF
Output capacitance <sup>b</sup>	C <sub>oss</sub>			120		
Reverse transfer capacitance <sup>b</sup>	C <sub>rss</sub>			80		
<b>Switching<sup>b</sup></b>						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 10V, R <sub>L</sub> = 5.5Ω, I <sub>D</sub> ≈ 3.6A, V <sub>GEN</sub> = 4.5V, R <sub>g</sub> = 6Ω		7	15	ns
Rise time	t <sub>r</sub>			55	80	
Turn-off delay time	t <sub>d(off)</sub>			16	60	
Fall time	t <sub>f</sub>			10	25	

**Notes :**

- a. Pulse Test : Pulse width ≤ 300µs, duty cycle ≤ 2%.
- b. These parameters have no way to verify.

## RATINGS AND CHARACTERISTIC CURVES

### Typical Characteristics

